



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Young-Hee MUN

Group Art Unit: 1765

Serial No.: 09/742,127

Examiner: M. Song

Filed: December 22, 2000.

For: METHOD FOR TREATING A SEMICONDUCTOR WAFER THERMALLY  
AND SEMICONDUCTOR WAFER FABRICATED BY THE SAME

TRANSMITTAL

Assistant Commissioner of Patents  
Washington, D.C. 20231

Sir:

Transmitted herewith is an Amendment Under Rule 1.111 for filing in the above-captioned patent application.

The fee has been calculated as shown below:

|   | Claims<br>Remaining<br>After<br>Amendment |   | Highest<br>Number<br>Previously<br>Paid For | Present<br>Extra | Small Entity<br>Rate Addit.<br>Fee | (or) | Other Than A<br>Small Entity<br>Rate Addit.<br>Fee |
|---|---|---|---|------------------|------------------------------------|------|--|
| Total   | 18  | - | 20 =  | 0                | x 09 = \$                          |      | x 18 = \$  |
| Indep.  | 05  | - | 05 =  | 0                | x 40 = \$                          |      | x 80 = \$  |
| ___ First Presentation of Multiple Dependent Claims |   |   |   |                  | +130 = \$                          |      | + 260 = \$   |
| Total Additional Fee                                |   |   |   |                  | \$                                 |      | \$   |

A check in the amount of \$\_\_\_\_\_ is attached for:

**XXXX** If a Petition for Extension of Time is necessary and the Petition and/or the check is not enclosed, this will act as the Petition and applicant herewith petitions the Commissioner to extend the time for response and charge any fees necessary under 37 CFR 1.17 (a)(1)-(5) to Deposit Account No. 06-1358. The Commissioner is also authorized to charge payment of any other additional fees associated with this communication or credit any overpayment to Deposit Account No. 06-1358. A duplicate copy of this sheet is attached.

Respectfully submitted,  
JACOBSON HOLMAN PLLC

By: Yoon S. Ham by Sign. C. Bailey  
Yoon S. Ham  
Reg. No. 45,307  
Reg. No. 40,495

400 Seventh Street, N.W.  
Washington, D.C. 20004-2201  
Atty. Docket: 12597/P66182US0  
Telephone: (202)638-6666  
Date: October 8, 2002  
YSH:SCB  
R:\HOME\SB\BAILEY\10-02\P66182US.TL



PATENT  
ATTY. DOCKET NO.: P66182US0

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Young-Hee MUN

Group Art Unit: 1765

Serial No.: 09/742,127

Examiner: M. Song

Filed: December 22, 2000

For: METHOD OF TREATING A SEMICONDUCTOR WAFER THERMALLY  
AND SEMICONDUCTOR WAFER FABRICATED BY THE SAME

**AMENDMENT UNDER RULE 1.111**

Assistant Commissioner  
of Patents  
Washington, D.C. 20231

October 8, 2002

Sir:

In response to the Office Action (Paper No. 7) dated July 9, 2002, kindly amend  
the above-identified patent application as follows:

**IN THE CLAIMS**

Please cancel claim 6 without prejudice or disclaimer, and amend claims 1, 8 and  
17-19 to read as follows:

1. (Amended) A method of treating a wafer thermally to remove defects contained in single  
crystalline semiconductor, the method comprising the steps of:

carrying out a heat treatment on the wafer at a temperature equal to or higher than  
1200 °C; and

carrying out a rapid thermal annealing on the wafer at a temperature equal to or  
lower than 800°C for a period having a duration of two minutes or less.

RECEIVED  
OCT 10 2002  
TC 1700 MAIL ROOM

#8A  
10/10/02  
mw

A-1  
2001